

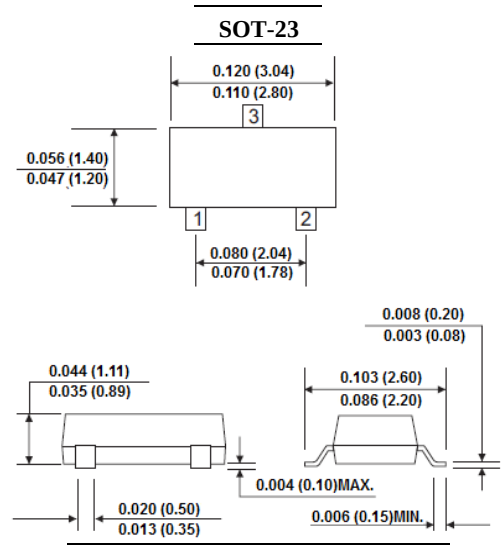
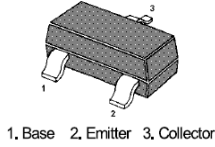


MMBT3904

NPN TRANSISTOR

FEATURES

- As complementary types the PNP transistors MMBT3904 is recommended
- Suffix "H" indicates Halogen-free parts, ex. MMBT3904H



Dimensions in inches and (millimeter)

Maximum Ratings($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	200	mA
Total Device Dissipation FR-5 Board ⁽¹⁾	P_D	225	mW
Derate above 25°C		1.8	mW / $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C} / \text{W}$
Total Device Dissipation Alumina Substrate ⁽²⁾	P_D	300	mW
Derate above 25°C		2.4	mW / $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C} / \text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

(1) Device on FR-5 = 1.0 x 0.75 x 0.062 in.

(2) Device on alumina substrate = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

Electrical Characteristics($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Min.	Max.	Unit
Collector-base breakdown voltage	$I_C = 10\mu\text{A}$	$V_{(BR)CBO}$	60	--	V
Collector-emitter breakdown voltage ⁽³⁾	$I_C = 1.0\text{mA}$	$V_{(BR)CEO}$	40	--	V
Emitter-base breakdown voltage	$I_E = 10\mu\text{A}$	$V_{(BR)EBO}$	6.0	--	V
Base cut-off current	$V_{CE} = 30\text{V}, V_{EB} = 3.0\text{V}$	I_{BL}	--	50	nA
Collector cut-off current	$V_{CE} = 30\text{V}, V_{EB} = 3.0\text{V}$	I_{CEX}	--	50	nA
DC current gain	$V_{CE} = 1.0\text{V}, I_C = 0.1\text{mA}$	h_{FE}	40	--	--
	$V_{CE} = 1.0\text{V}, I_C = 1.0\text{mA}$		70	--	
	$V_{CE} = 1.0\text{V}, I_C = 10\text{mA}$		100	300	
	$V_{CE} = 1.0\text{V}, I_C = 50\text{mA}$		60	--	
	$V_{CE} = 1.0\text{V}, I_C = 100\text{mA}$		30	--	
Collector-emitter saturation voltage ⁽³⁾	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$	$V_{CE(sat)}$	--	0.2	V
	$I_C = 50\text{mA}, I_B = 5.0\text{mA}$			0.3	
Base-emitter saturation voltage ⁽³⁾	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$	$V_{BE(sat)}$	0.65	0.85	V
	$I_C = 50\text{mA}, I_B = 5.0\text{mA}$		--	0.95	

(3) Pulse Test: Pulse Width <300 μs , Duty Cycle <2.0%.



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Electrical Characteristics($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Min.	Max.	Unit
Current-gain — bandwidth product	$V_{CE} = 20\text{V}$, $I_C = 10\text{mA}$, $f = 100\text{MHz}$	f_T	300	--	MHz
Output capacitance	$V_{CB} = 5.0\text{V}$, $I_E = 0$, $f = 1.0\text{ MHz}$	C_{obo}	--	4.0	pF
Input capacitance	$V_{BE} = 0.5\text{V}$, $I_C = 0$, $f = 1.0\text{ MHz}$	C_{ibo}	--	8.0	pF
Input impedancen	$V_{CE} = 10\text{V}$, $I_C = 1.0\text{mA}$, $f = 1.0\text{ kHz}$	h_{ie}	1.0	10	$k\Omega$
Voltage feedback Ratio	$V_{CE} = 10\text{V}$, $I_C = 1.0\text{mA}$, $f = 1.0\text{ kHz}$	h_{re}	0.5	8.0	$\times 10^{-4}$
Small-signal current gain	$V_{CE} = 10\text{V}$, $I_C = 1.0\text{mA}$, $f = 1.0\text{ kHz}$	h_{fe}	100	400	--
Output admittance	$V_{CE} = 10\text{V}$, $I_C = 1.0\text{mA}$, $f = 1.0\text{ kHz}$	h_{oe}	1.0	40	μmhos
Noise figure	$V_{CE} = 5.0\text{V}$, $I_C = 100\mu\text{A}$, $R_S = 1.0k\ \Omega$, $f = 1.0\text{ kHz}$	NF	--	5.0	dB
Delay time	$V_{CC} = 3.0\text{V}$, $V_{BE} = -0.5\text{V}$ $I_C = 10\text{mA}$, $I_{B1} = 1.0\text{mA}$	t_d	--	35	nS
Rise time		t_r	--	35	nS
Storage time	$V_{CC} = 3.0\text{V}$, $I_C = 10\text{mA}$ $I_{B1} = I_{B2} = 1.0\text{mA}$	t_s	--	200	nS
Fall time		t_f	--	50	nS

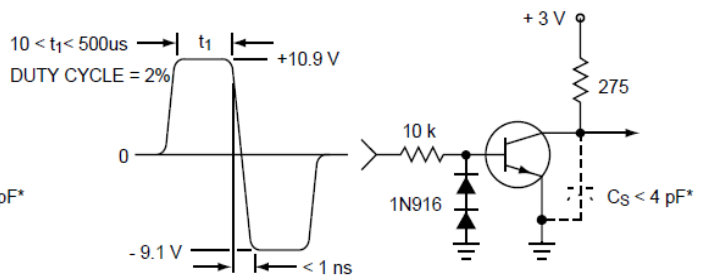


Figure 2. Storage and Fall Time Equivalent Test Circuit

RATINGS AND CHARACTERISTIC CURVES

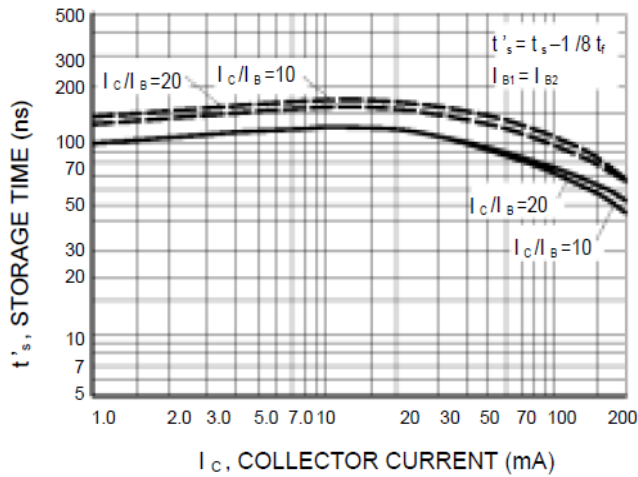


Figure 7. Storage Time

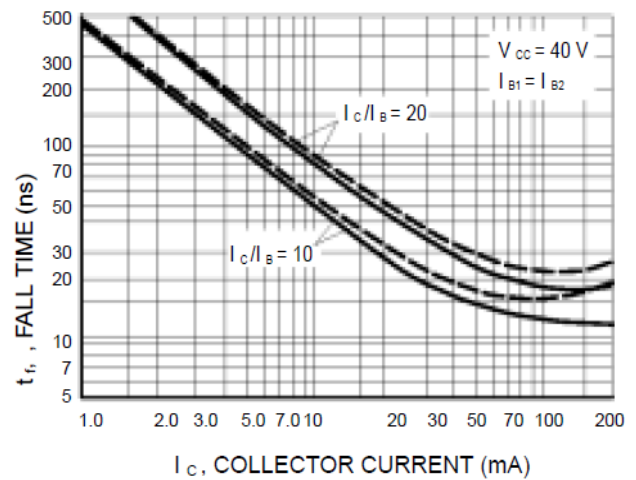


Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE VARIATIONS

($V_{CE} = 5.0 V$, $T_A = 25^\circ C$, Bandwidth = 1.0 Hz)

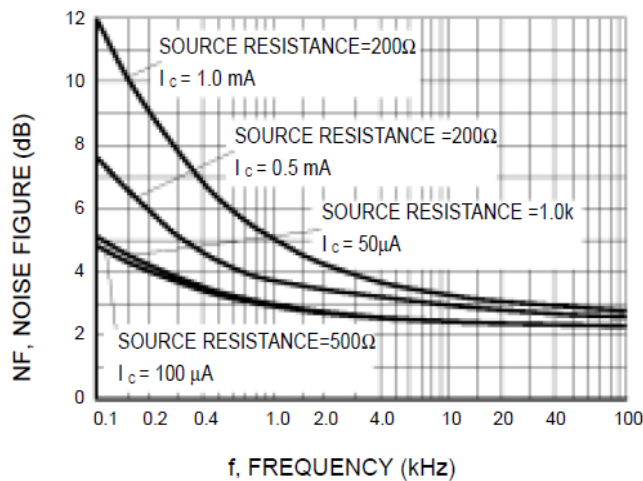


Figure 9.

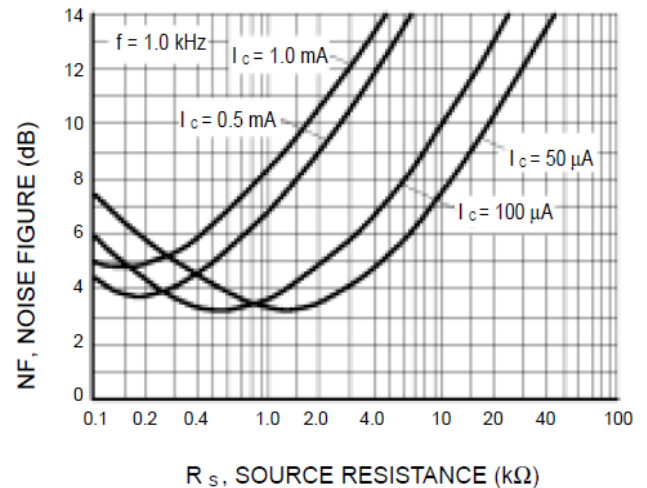


Figure 10.

h PARAMETERS

($V_{CE} = 10 V$, $f = 1.0 kHz$, $T_A = 25^\circ C$)

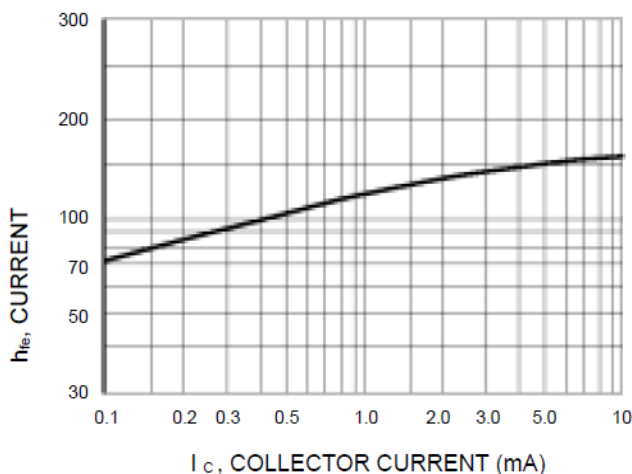


Figure 11. Current Gain

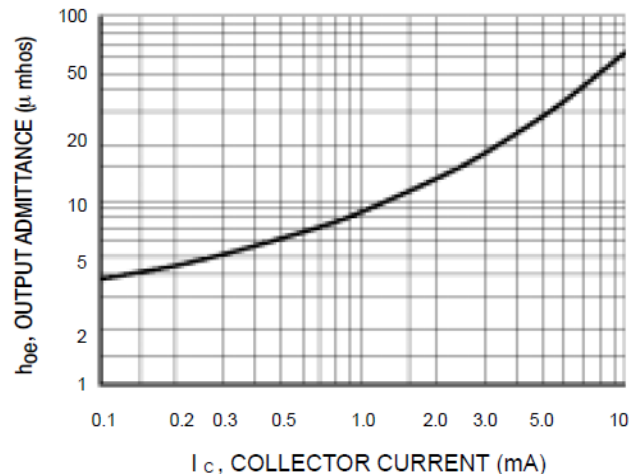


Figure 12. Output Admittance



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RATINGS AND CHARACTERISTIC CURVES

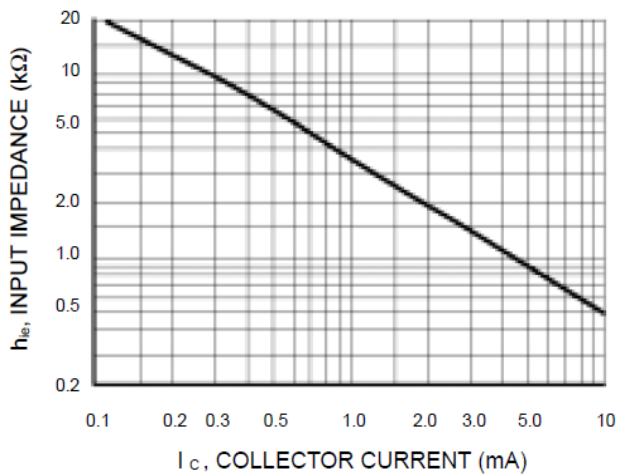


Figure 13. Input Impedance

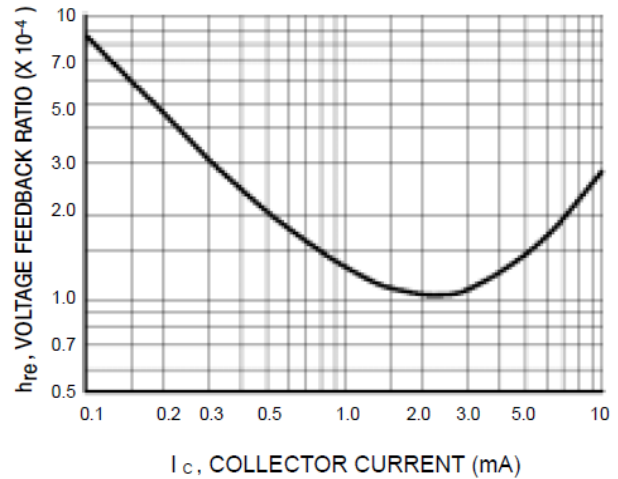


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

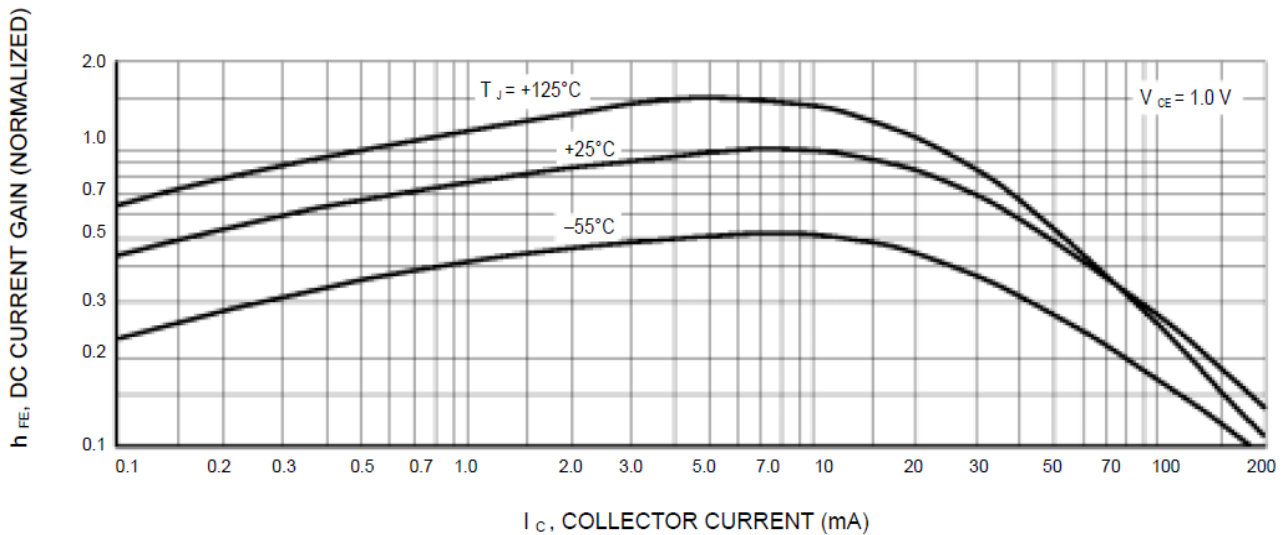


Figure 15. DC Current Gain

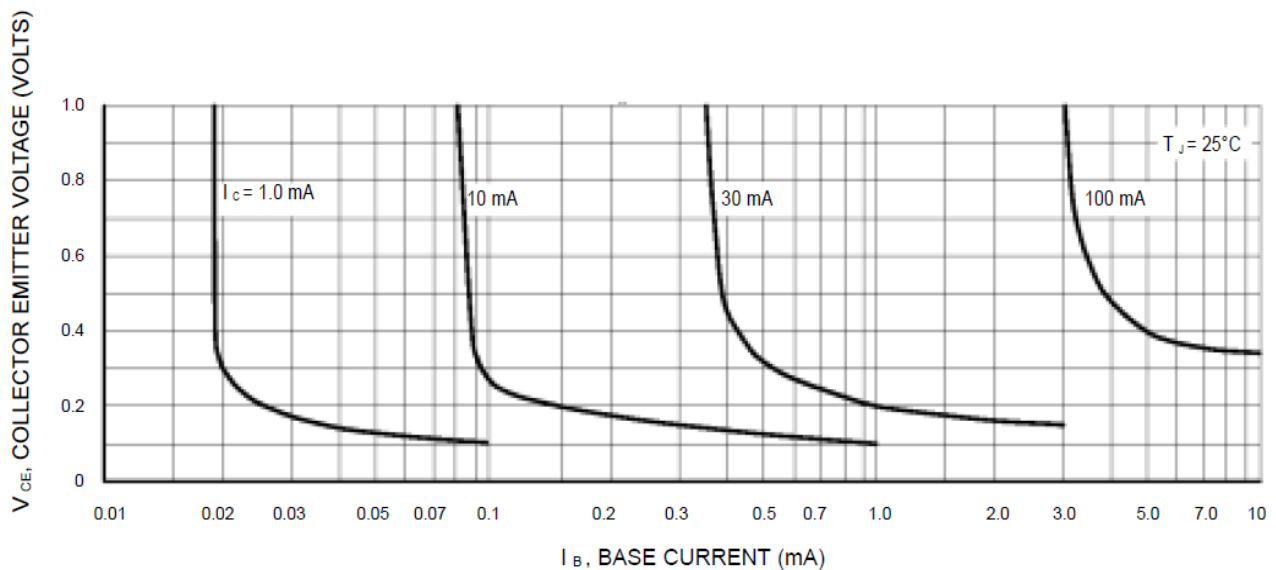


Figure 16. Collector Saturation Region



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RATINGS AND CHARACTERISTIC CURVES

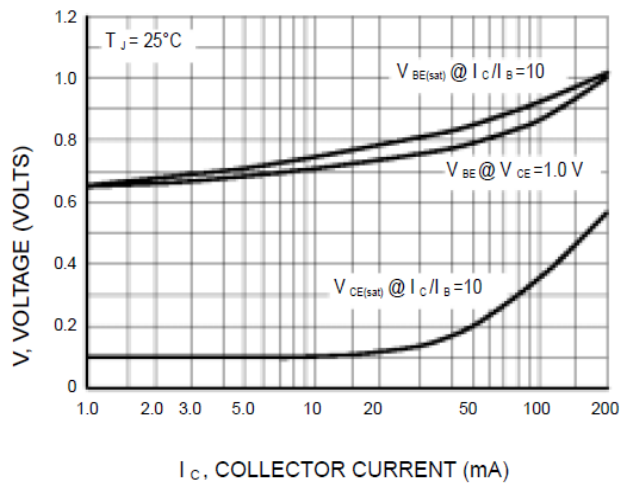


Figure 17. "ON" Voltages

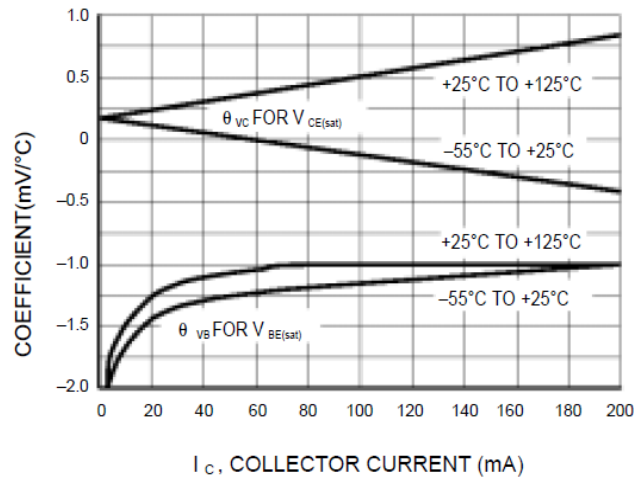


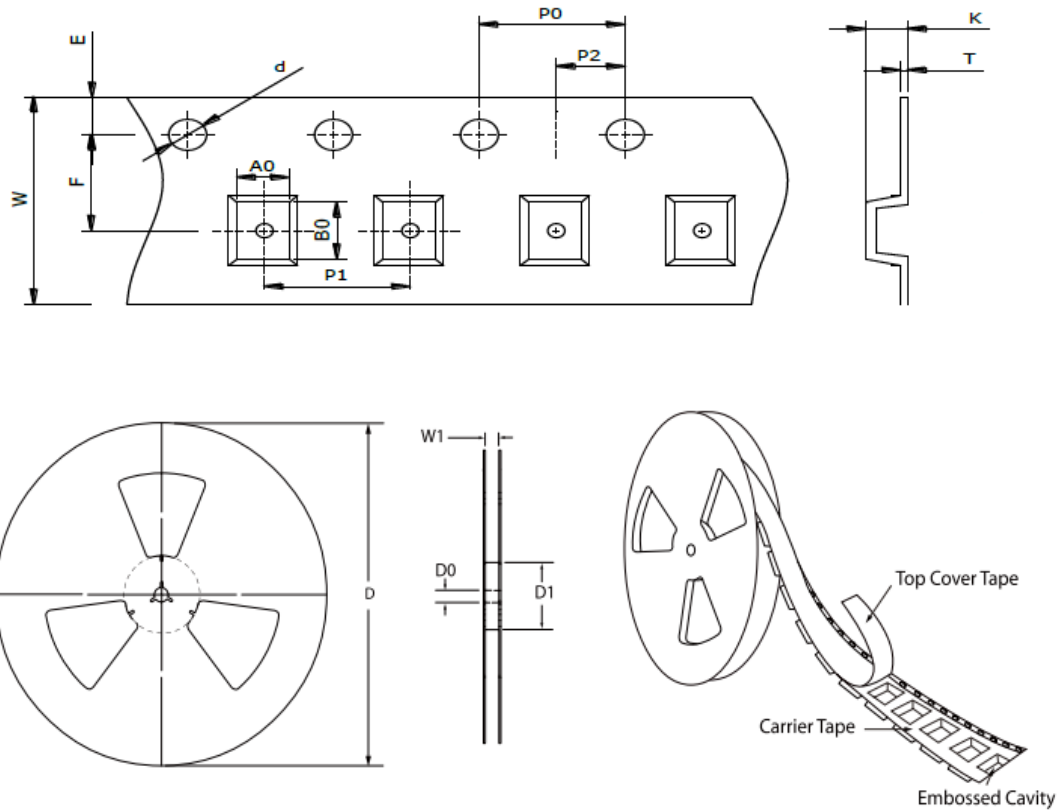
Figure 18. Temperature Coefficients



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TAPE & REEL SPECIFICATION



Item	Symbol	SOT-23
Carrier width	A_0	3.10 ± 0.10
Carrier length	B_0	2.70 ± 0.10
Carrier depth	K	1.15 ± 0.10
Sprocket hole	d	1.50 ± 0.10
Reel outside diameter	D	178.00 ± 2.00
Feed hole width	D_0	13.00 ± 0.20
Reel inner diameter	D_1	MIN. 54.00
Sprocket hole position	E	1.75 ± 0.10
Punch hole position	F	3.50 ± 0.10
Sprocket hole pitch	P_0	4.00 ± 0.10
Punch hole pitch	P_1	4.00 ± 0.10
Embossment center	P_2	2.00 ± 0.10
Overall tape thickness	T	0.20 ± 0.05
Tape width	W	8.00 ± 0.20
Reel width	W1	MAX. 13.50

ORDER INFORMATION

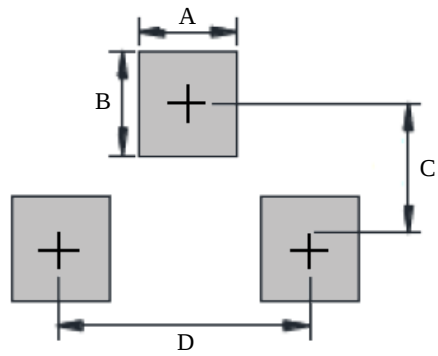
Package	Reel Size	Quantity
SOT-23	7"	3,000



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SUGGESTED SOLDER PAD LAYOUT



Unit : mm

PACKAGE	A	B	C	D
SOT-23	0.80	0.80	2.02	1.90